



Monolithic Photodiode Array - Chip

Features

- Dielectrically Isolated Diodes
- Aluminum Wire bondable
- Backside Metallization - Gold
- Die Attach methods: Eutectic or Epoxy

Electrical Characteristics @ 25 °C

SYMBOL	CHARACTERISTIC	CONDITIONS	MIN	TYP	MAX	UNITS
VOC	Open Circuit Voltage	10 mW/cm ² , wavelength = 850 nm	10			Volts
ISC	Short Circuit Current	10 mW/cm ² , wavelength = 850 nm	3.5			uA
VB	Reverse Breakdown Voltage	IR = 10 uA	20			Volts

